AUK Semiconductor

SDB110Q

Schottky Barrier Diode

Features

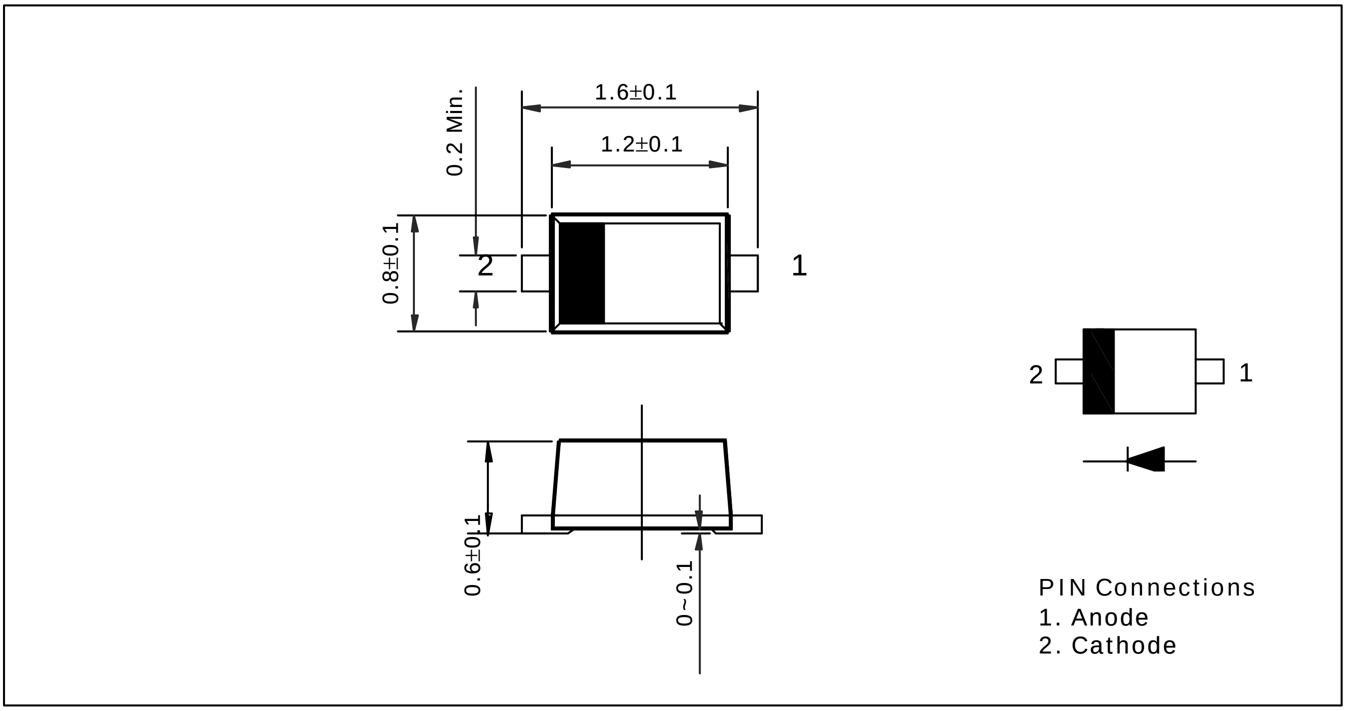
- Low power rectified
- Silicon epitaxial type
- Battery changing diode

Ordering Information

Type No.	Marking	Package Code
SDB110Q	S3	SOD-523

Outline Dimensions

unit : mm



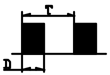
PIN Connections
1. Anode
2. Cathode

Absolute maximum ratings

(Ta=25° C)

Characteristic	Symbol	Ratings	Unit
Reverse voltage	V_R	10	V
Repetitive peak forward current	I_{FRM}*	0.5	A
Forward current	I_F	30	mA
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ 150	°C

* : δ = D/T =0.33
(T<1S)



* : Unit ratings. Total rating=Unit rating×1.5

Electrical Characteristics

(Ta=25° C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage 1	$V_{F(1)}$	I_F=1mA	0.1	-	0.3	V
Forward voltage 2	$V_{F(2)}$	I_F=10mA	-	-	0.35	V
Reverse current	I_R	V_R=5V	-	-	0.5	μA
ESD-Capability	-	C=200pF, RL=100 Both forward reverse direction 5 pulse	225	-		V

Electrical Characteristic Curves

Fig. 1 I_F-V_F

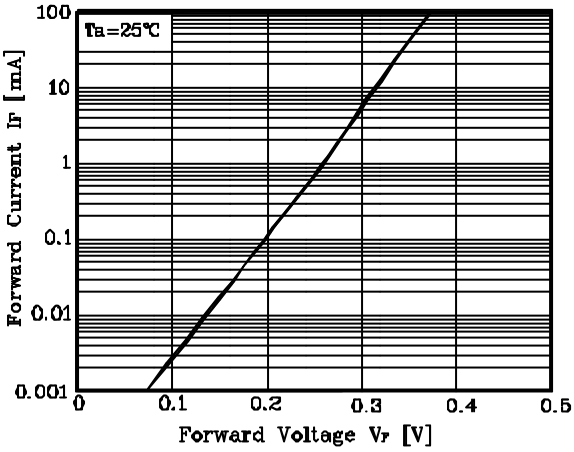


Fig. 2 I_R -V_R